

## 10MQ100N-S

Technical Data Data Sheet N1371, Rev. C

RoHS 🗭

# **10MQ100N-S SCHOTTKY RECTIFIER**



Anode

### Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T⊾=105°C, rectangular wave form	1.5	А
DC Current	I <sub>F(DC)</sub>	DC@T <sub>L</sub> =120°C	2.1	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	36	А

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 1 A, Pulse, TJ = 25 °C	0.76	0.78	V
		@ 1.5 A, Pulse, T <sub>J</sub> = 25 °C	0.79	0.85	v
	V <sub>F2</sub>	@ 1 A, Pulse, Tյ = 125 °C	0.61	0.63	V
		@ 1.5A, Pulse, T <sub>J</sub> = 125 °C	0.65	0.68	v
Reverse Current*	I <sub>R1</sub>	$@V_R$ = rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 25 °C	0.1	100	uA
	I <sub>R2</sub>	$@V_R$ = rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 125 °C	0.05	1	mA
Junction Capacitance	Ст	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C, f <sub>SIG</sub> = 1MHz	36	38	PF
Typical Series Inductance	Ls	Measured lead to lead 5 mm from 2.0 -		-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

\* Pulse width < 300 μs, duty cycle < 2%

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## **Circuit Diagram**

Cathode



# 10MQ100N-S

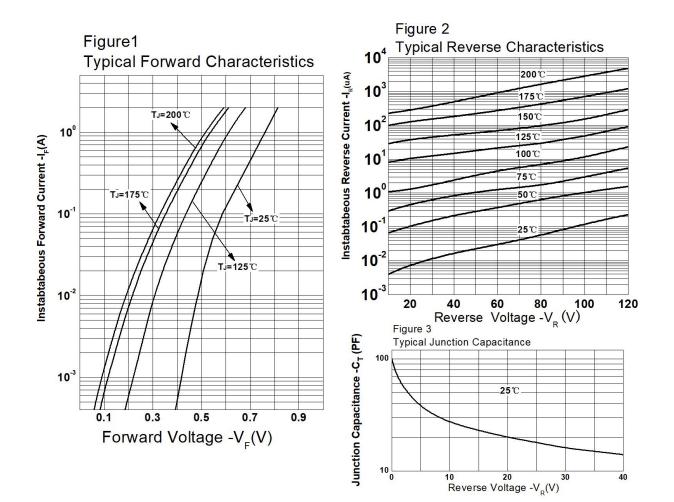
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## Thermal-Mechanical Specifications:

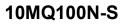
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	-	80	°C/W
Approximate Weight	wt	-	0.06	g
Case Style		SMA		

## **Ratings and Characteristics Curves**



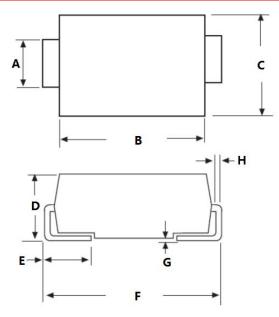


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## Mechanical Dimensions SMA(Millimeters/Inches)



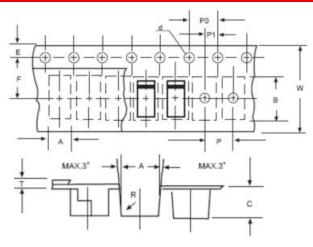
SYMBOL	Millimeters		Inches	
STMBOL	Min.	Max.	Min.	Max.
A	1.25	1.65	0.049	0.065
В	3.95	4.60	0.156	0.181
С	2.25	2.95	0.089	0.116
D	1.95	2.90	0.077	0.114
E	0.75	1.60	0.030	0.063
F	4.80	5.60	0.189	0.220
G	0.05	0.20	0.002	0.008
Н	0.15	0.41	0.006	0.016

### **Ordering Information**

Device	Package	Shipping	
10MQ100N-S	SMA (Pb-Free)	5000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## Carrier Tape & Reel Specification SMA



SA1J	
XXXXXX	- 22

**Marking Diagram** 

Where XXXXX is YYWWL

s

A 1

J

L

ΥY

WW

- = Device Type = Package Type
- = Forward Current (1A)
- = Reverse Voltage (100V)
- = Year = Week

= Lot Number

Cautions: Molding resin Eboxv resin UL:94V-0

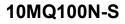
SYMBOL	Millimeters			
STIVIBOL	Min.	Max.		
A	2.97	3.17		
В	5.70	5.90		
С	2.32	2.52		
d	1.40	1.60		
E	1.40	1.60		
F	5.60	5.70		
Р	3.90	4.10		
P0	3.90	4.10		
P1	1.90	2.10		
Т	0.25	0.35		
W	11.80	12.20		

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